



# TIGER ELECTRONIC CO.,LTD



## KTC3200

EPITAXIAL PLANAR NPN TRANSISTOR



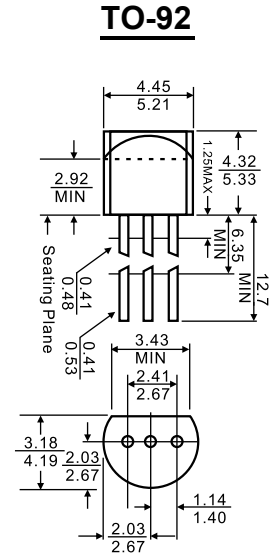
1. EMITTER
2. COLLECTOR
3. BASE

### FEATURES

- The KTC3200 is a transistor for low frequency and low noise applications. This device is designed to lower noise figure in the region of low signal source impedance, and to lower the pulse noise. This is recommended for the first stages of equalizer amplifiers.
- Low Noise
  - : NF=4dB(Typ.), Rg=100Ω, V<sub>CE</sub>=6V, I<sub>C</sub>=100μA, f=1kHz
  - : NF=0.5dB(Typ.), Rg=1kΩ, V<sub>CE</sub>=6V, I<sub>C</sub>=100μA, f=1kHz.
- Low Pulse Noise : Low 1/f Noise.
- High DC Current Gain : h<sub>FE</sub>=200~700.
- High Breakdown Voltage : V<sub>CEO</sub>=120V .

### MAXIMUM RATINGS (T<sub>a</sub>=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	120	V
Collector-Emitter Voltage	V <sub>CEO</sub>	120	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current	I <sub>C</sub>	100	mA
Emitter Current	I <sub>E</sub>	-100	mA
Collector Power Dissipation	P <sub>C</sub>	625	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C



Dimensions in inches and (millimeters)

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C)

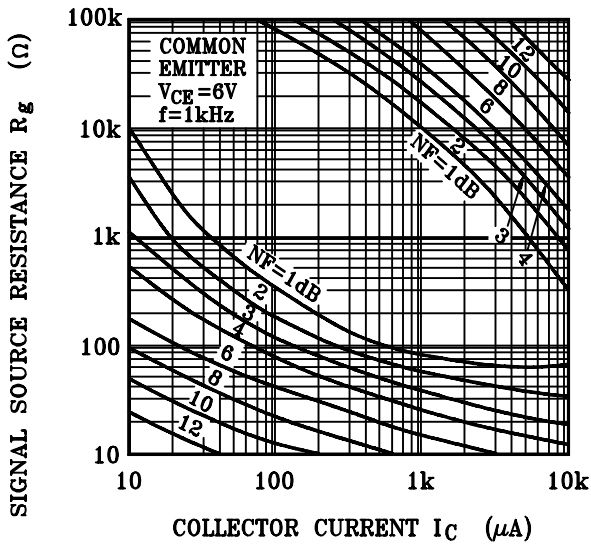
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0	-	-	100	nA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0	-	-	100	nA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	120	-	-	V
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> =6V, I <sub>C</sub> =2mA	200	-	700	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	-	-	0.3	V
Base-Emitter Voltage	V <sub>BE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =2mA	-	0.65	-	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	-	100	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz	-	3.0	-	pF
Noise Figure	NF	V <sub>CE</sub> =6V, I <sub>C</sub> =100μA, f=10Hz, Rg=10kΩ	-	-	6.0	dB
		V <sub>CE</sub> =6V, I <sub>C</sub> =100μA, f=1kHz, Rg=10kΩ	-	-	2.0	
		V <sub>CE</sub> =6V, I <sub>C</sub> =100μA, f=1kHz, Rg=100Ω	-	4.0	-	

Note : h<sub>FE</sub> Classification GR:200~400, BL:350~700

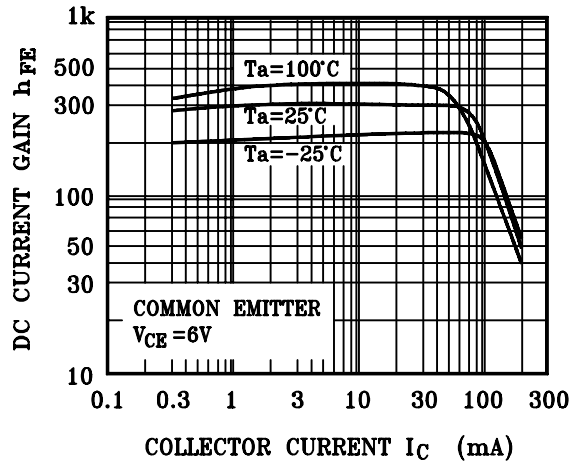
# KTC3200

EPITAXIAL PLANAR NPN TRANSISTOR

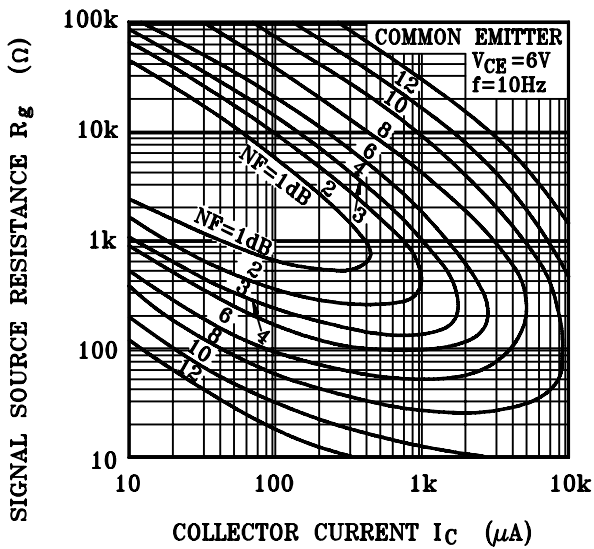
NF -  $R_g$ ,  $I_C$



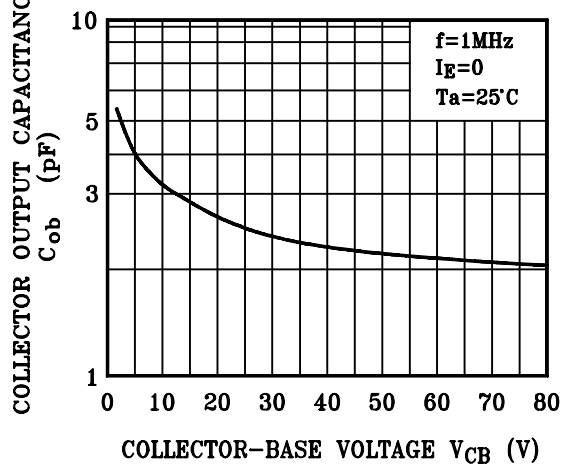
$h_{FE}$  -  $I_C$



NF -  $R_g$ ,  $I_C$



$C_{ob}$  -  $V_{CB}$



h PARAMETER -  $V_{CE}$

